

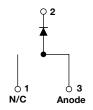
HALOGEN

FREE

# HEXFRED® Ultrafast Soft Recovery Diode, 16 A



D<sup>2</sup>PAK (TO-263AB)



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub> 16 A								
$V_{R}$	1200 V							
V <sub>F</sub> at I <sub>F</sub>	2.3 V							
t <sub>rr</sub> (typ.)	30 ns							
T <sub>J</sub> max.	150 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single							

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA16TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V <sub>R</sub>		1200	V	
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	16		
Single pulse forward current	I <sub>FSM</sub>		190	Α	
Maximum repetitive forward current	I <sub>FRM</sub>		64		
Maximum navver discination	П	T <sub>C</sub> = 25 °C	151	14/	
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	60	W	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C	





<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	1200	-	-				
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 16 A		-	2.5	3.0	V		
		I <sub>F</sub> = 32 A	See fig. 1	-	3.2	3.93			
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C		-	2.3	2.7			
Maximum reverse	ı	V <sub>R</sub> = V <sub>R</sub> rated	See fig. 2	-	0.75	20			
leakage current	I <sub>RM</sub>	$T_J = 125  ^{\circ}\text{C},  V_R = 0.8  \text{x}  V_R  \text{rated}$	See lig. 2	-	375	2000	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		-	27	40	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from page 1	-	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	30	-	ns		
Reverse recovery time See fig. 5 and 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	90	135			
dee lig. o dita to	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	164	245			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	5.8	10	- A - nC		
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 16 A	-	8.3	15			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 200 V	-	260	675			
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	VR - 200 V	-	680	1838			
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-			
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	-	A/μs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	0.83	K/W			
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	I NVV			
Weight			-	2.0	-	g			
vveignt			-	0.07	-	oz.			
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	HFA16TB120S						

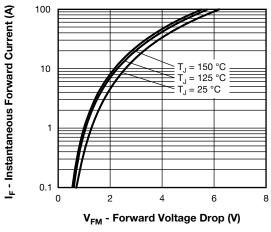


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

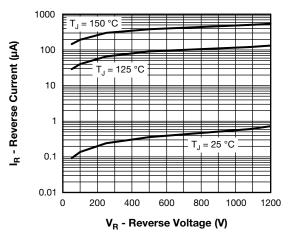


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

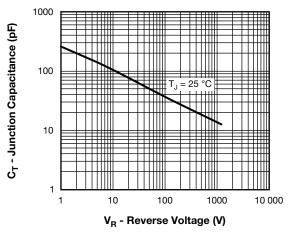


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

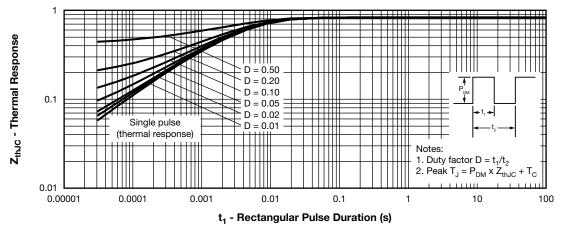


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

#### www.vishay.com

## Vishay Semiconductors

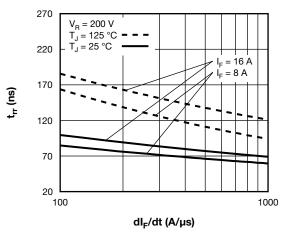


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

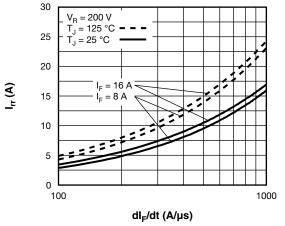


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)

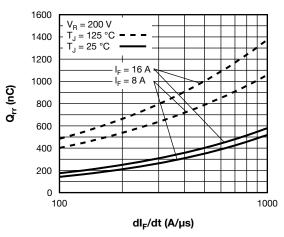


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

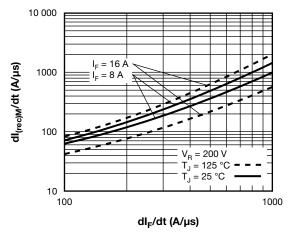
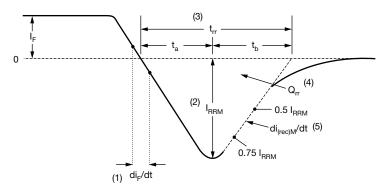


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt (Per Leg)



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\text{rr}}$  area under curve defined by  $\mathbf{t}_{\text{rr}}$  and  $\mathbf{I}_{\text{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

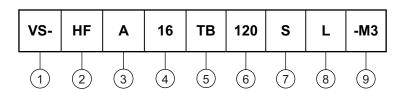
(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

#### Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Process designator: A = electron irradiated

Current rating (16 = 16 A)

5 - Package outline (TB = TO-220, 2 leads)

6 - Voltage rating (120 = 1200 V)

7 -  $S = D^2PAK (TO-263AB)$ 

8 - • None = tube

• L = tape and reel (left oriented)

• R = tape and reel (right oriented)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TB120S-M3	50	1000	Antistatic plastic tube						
VS-HFA16TB120SR-M3	800	800	13" diameter reel						
VS-HFA16TB120SL-M3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96164</u>						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	NOTES		MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3	
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3	
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3	
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625		
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110		
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3	
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070		
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208		

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



## **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Rectifiers category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

70HFR40 RL252-TP 150KR30A 1N5397 NTE5841 NTE6038 SCF5000 1N4002G 1N4005-TR JANS1N6640US 481235F

RRE02VS6SGTR 067907F MS306 70HF40 T110HF60 T85HFL60S02 US2JFL-TP A1N5404G-G CRS04(T5L,TEMQ) ACGRA4007-HF

ACGRB207-HF CLH03(TE16L,Q) ACGRC307-HF ACEFC304-HF NTE6356 NTE6359 NTE6002 NTE6023 NTE6039 NTE6077

85HFR60 40HFR60 1N1186RA 70HF120 85HFR80 D126A45C SCF7500 D251N08B SCHJ22.5K SM100 SCPA2 SCH10000 SDHD5K

VS-12FL100S10 ACGRA4001-HF D1821SH45T PR D1251S45T NTE5990 NTE6358